D9-4-808-1000

Application

Laser Projector

Measuring equipment

Property

Wavelength λ = 808 nm

Output Power = 1000mW

Package Type = φ 9.0mm

Introduction

Egismos currently markets AlGaAs infrared laser diodes in the 780nm ~ 1550nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer. Egismos laser diodes are highly rated in a broad range of applications including, but not limited to, laser pointers, laser barcode scanners, diode laser equipments, medical instruments and aerospace applications.

Laser Diode Key features

Absolute Maximum Rating at Tc=25℃

Items		Symbols	Values	Unit
Operating Current power		P_o	1000	mW
Reverse Voltage	LD	V_R	2	V
Operating Temperature		T_{case}	-10~+40	℃
Storage Temperature		T_s	-40~+85	℃

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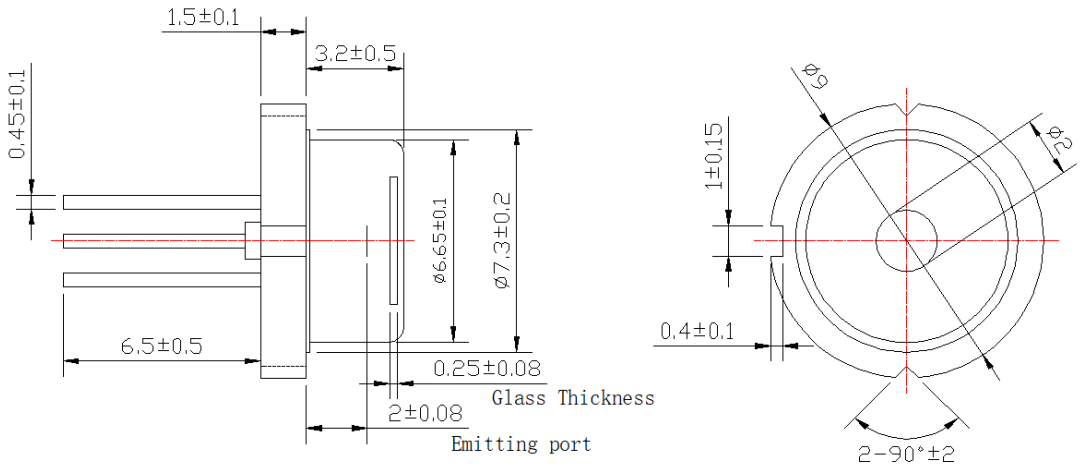
808nm Infrared Laser Diode

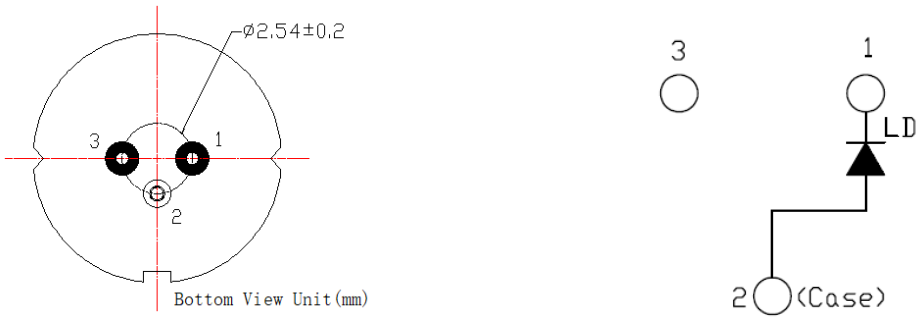
Electrical and Optical Characteristics at Tc=25℃

Item	Symbols	Min	Typ.	Max.	Unit	Condition
Threshold Current	I_{th}	-	240		mA	-
Operating Current	I_{op}	-	1200	1500	mA	Po=1000mW
Operating Voltage	V_{op}	-	2.0	2.6	V	Po=1000mW
Peak Wavelength	λ p	803	808	813	nm	Po=1000mW
Beam Divergence (FWHM)	$\theta_{//}$	-	9	12	deg	Po=1000mW
Beam Divergence (FWHM)	$\theta_{\perp}$	-	30	40	deg	Po=1000mW
Slope Efficiency	SE	-	1	-	W/A	-

Package Drawing



ELECTRICAL CONNECTION



Specifications are subject to change without notice.

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